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Supporting Information

The novel mechanism in understanding a strong enhancement of photoluminescence quantum yield in large-area monolayer MoS₂ grown by CVD

Kishore K. Madapu,*^a C. Abinash Bhuyan,^a S. K. Srivastava,^b and Sandip Dhara*^a

Email: madupu@igcar.gov.in, dhara@igcar.gov.in

^{a.} Surface and Nanoscience Division, Indira Gandhi Centre for Atomic Research, Homi Bhabha

National Institute, Kalpakkam-603 102, India

^{b.} Materials Physics Division, Indira Gandhi Centre for Atomic Research, Kalpakkam-603 102,

India

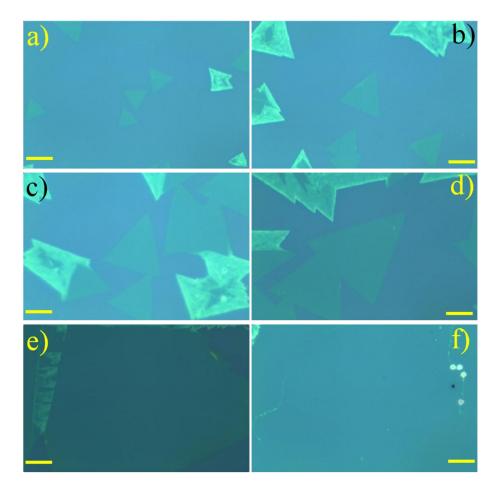


Figure S1. (a-d) Optical micrographs of MoS_2 monolayer structures grown on Si(300 nm)/Si. (e, f) A grain-free large area of MoS_2 monolayers. The scale shown in the figures corresponds to 10 μ m.

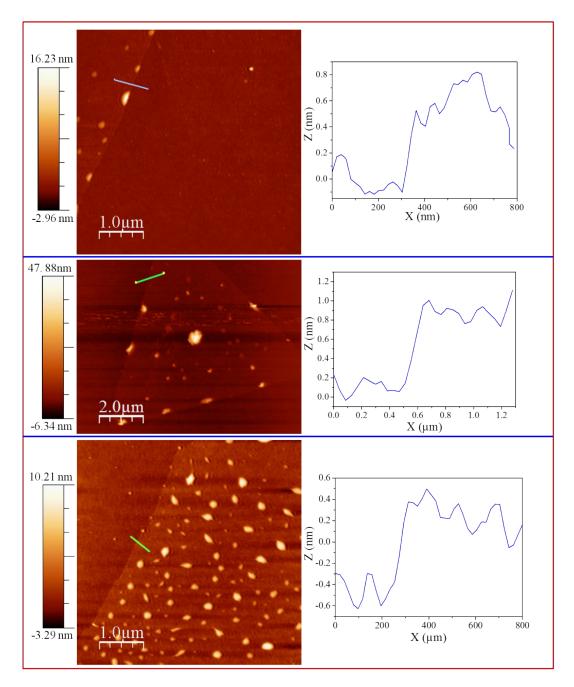


Figure S2. AFM topography analyses showing the thickness of the MoS_2 layers less than 0.9 nm confirming the formation of a monolayer.

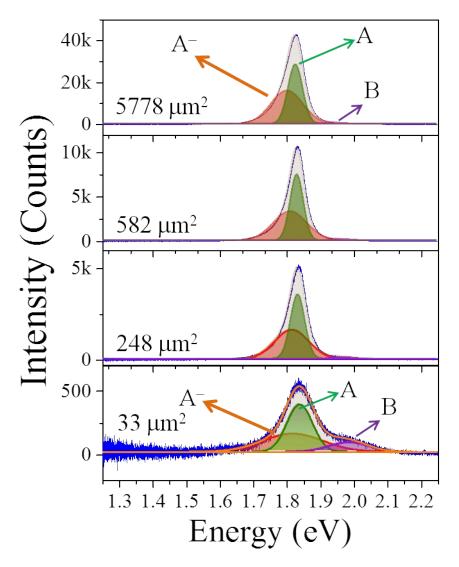


Figure S3. PL spectra of monolayer MoS₂ with different areas fitted with Gaussian functions.

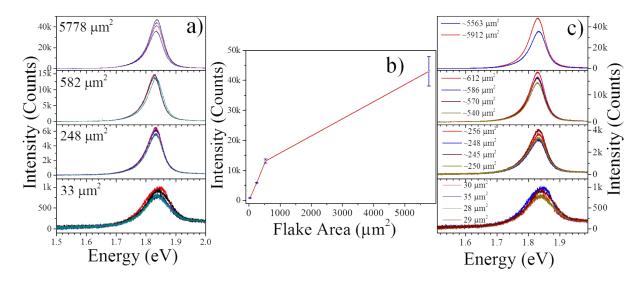


Figure S4. a) PL spectra collected at each flake area at different locations around the centre region. b) Variation of mean PL intensity with flake area. c) PL spectra collected at arbitrary flakes with the equivalent area.

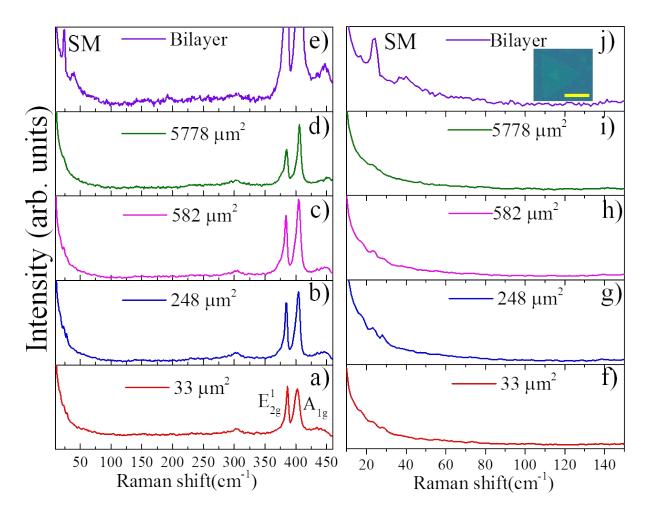


Figure S5. (a)-(d) Raman spectra of the 1L-MoS₂ flakes with varying sizes (area) and (f)-(i) corresponding zoomed low-frequency region, respectively. (e) Raman analyses of the bilayer MoS₂ flakes and (j) corresponding zoomed low-frequency region. The optical image of the bilayer structure is shown in the inset of (j) and the scale shown in the figure corresponds to the 5 μ m.

The absence of the shear mode (SM) in all 1L-MoS₂ flakes (a-d) reveals that the flakes are monolayer structures. For comparison, bilayer MoS₂ shows the SM mode (e and j) in the Raman spectra. The low-frequency region is zoomed (f-i) to show a clear absence of SM mode for monolayer flakes.

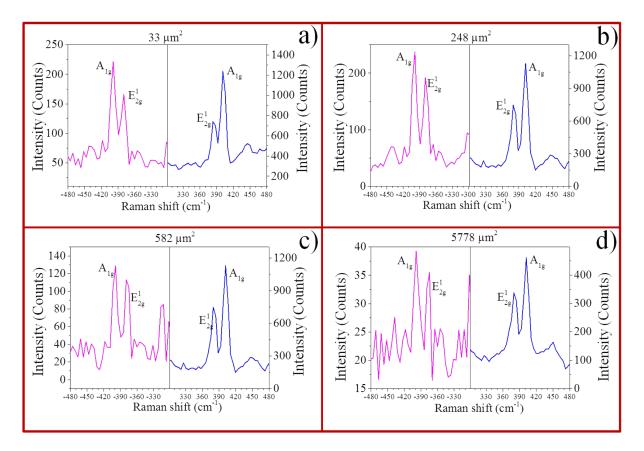


Figure S6. Stokes and anti-Stokes Raman spectra of MoS_2 monolayers with different areas.

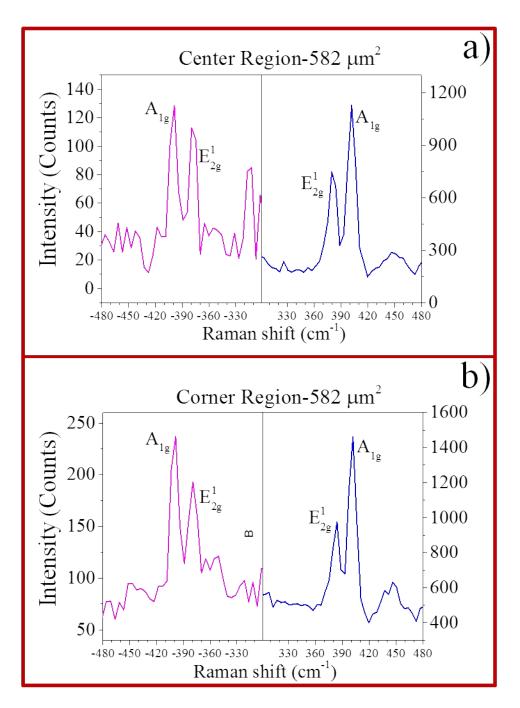


Figure S7. Stokes and anti-Stokes Raman spectra of MoS_2 monolayer flake (~582 μ m²) collected at (a) Center Region and (b) Corner Region.

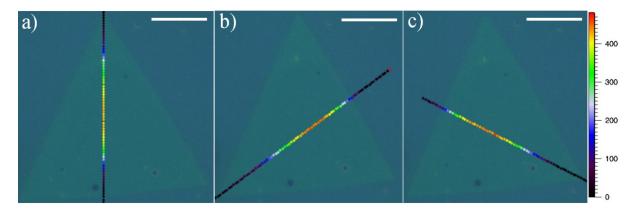


Figure S8. a)-c) Line imaging of PL peak intensity along the medians of triangular flake.

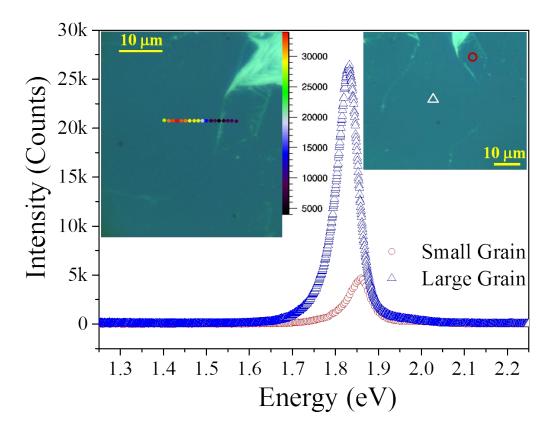


Figure S9. Typical PL spectra of 1L-MoS₂ collected from the large (~2663 μ m²) and small (~135 μ m²) grains. The centres of the collected regions are indicated by open triangle and circle in the optical micrograph, respectively (right hand side inset). PL line image is shown covering the part of the large and small grains (left side inset).

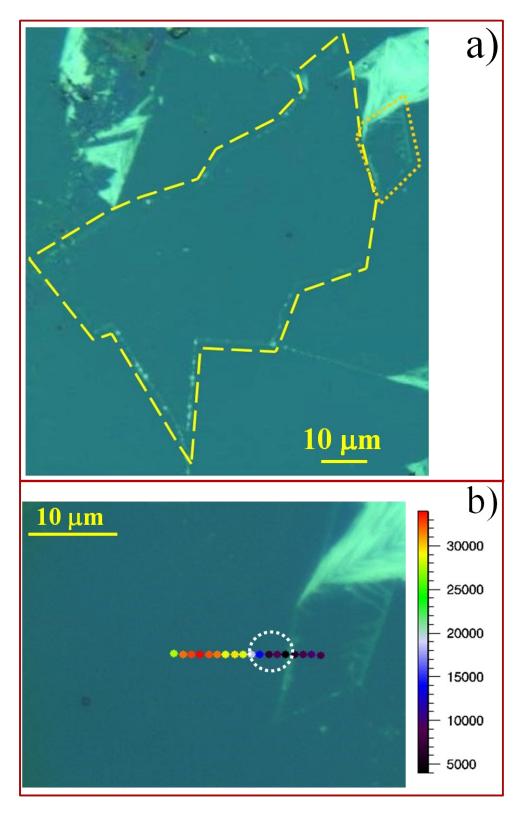


Figure S10. a) Optical micrograph of PL imaging area showing large grain and small grain with dashed and dotted boundaries, respectively. b) PL line image is shown covering the part of the large and small grains. PL intensity reduction near the grain boundary region indicated by a dotted ellipse.

Table S1: Peak position and intensities of A exciton and trion, the difference in the peak positions, and calculated carrier density values of each flake area. The values are extracted using the Gaussian fits of PL spectra.

Area	$P(A^{-})$	<i>I</i> (A-)	$P(\mathbf{A})$	I(A)	$P(\mathbf{B})$	I(A)	$D(A-A^{-})$	<i>I</i> (A)/ <i>I</i> (A ⁻)	n _e
μm ²	eV		eV		eV		meV		$\times 10^{13} \text{ cm}^{-2}$
33	1.816	32.15	1.837	35.46	1.983	11.02	21	1.103	2.76
248	1.813	210.72	1.834	189.90	1.966	12.13	21	0.901	2.25
532	1.811	414.67	1.831	373.75	1.965	13.27	20	0.901	2.25
5778	1.802	1915.64	1.827	1578.27	1.936	61.25	25	0.824	2.06

P-Position of the peak; *I*-Integrated intensity of peak; *D*-Difference in the peak positions of the A-exciton (A) and trion (A⁻); n_e -Carrier density